

# Michael Kneissl

## List of Publications by Year in descending order

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391  
papers

10,835  
citations

43973

48  
h-index

46693

89  
g-index

395  
all docs

395  
docs citations

395  
times ranked

5231  
citing authors

#	ARTICLE	IF	CITATIONS
1	Impact of operation parameters on the degradation of 233nm AlGaIn-based far-UVC LEDs. Journal of Applied Physics, 2022, 131, .	1.1	17
2	Spectrally pure far-UVC emission from AlGaIn-based LEDs with dielectric band pass filters. Journal Physics D: Applied Physics, 2022, 55, 205105.	1.3	3
3	Application of 233nm far-UVC LEDs for eradication of MRSA and MSSA and risk assessment on skin models. Scientific Reports, 2022, 12, 2587.	1.6	23
4	UV LED reliability: degradation mechanisms and challenges. , 2022, , .		2
5	The influence of threading dislocations propagating through an AlGaIn UVC LED. Applied Physics Letters, 2022, 120, .	1.5	6
6	A 310 nm Optically Pumped AlGaIn Vertical-Cavity Surface-Emitting Laser. ACS Photonics, 2021, 8, 135-141.	3.2	18
7	Influence of the hydrogen level in (InAlGa)N-based laser diodes on the stability of the device's operating voltage. Journal Physics D: Applied Physics, 2021, 54, 135103.	1.3	2
8	Origin of defect luminescence in ultraviolet emitting AlGaIn diode structures. Applied Physics Letters, 2021, 118, .	1.5	4
9	Electrical and optical characteristics of highly transparent MOVPE-grown AlGaIn-based tunnel heterojunction LEDs emitting at 232nm. Photonics Research, 2021, 9, 1117.	3.4	13
10	Light extraction efficiency and internal quantum efficiency of fully UVC-transparent AlGaIn based LEDs. Journal Physics D: Applied Physics, 2021, 54, 335101.	1.3	16
11	Advances towards deep-UV light emitting diode technologies. , 2021, , .		2
12	Skin tolerant inactivation of multiresistant pathogens using far-UVC LEDs. Scientific Reports, 2021, 11, 14647.	1.6	37
13	Quantification of Trace-Level Silicon Doping in Al <sub>x</sub> Ga <sub>1-x</sub> N Films Using Wavelength-Dispersive X-Ray Microanalysis. Microscopy and Microanalysis, 2021, 27, 696-704.	0.2	1
14	Effect of Inhomogeneous Broadening in Ultraviolet III-Nitride Light-Emitting Diodes. Materials, 2021, 14, 7890.	1.3	10
15	Effect of unevenly-distributed V pits on the optical and electrical characteristics of green micro-light emitting diode. Journal Physics D: Applied Physics, 2020, 53, 045106.	1.3	3
16	AlN overgrowth of nano-pillar-patterned sapphire with different offcut angle by metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2020, 531, 125343.	0.7	13
17	Improving AlN Crystal Quality and Strain Management on Nanopatterned Sapphire Substrates by High-Temperature Annealing for UVC Light-Emitting Diodes. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900796.	0.8	15
18	Improvement in the Reliability of AlGaInP-Based Light-Emitting Diode Package Using Optimal Silicone and Leadframe Structure. ECS Journal of Solid State Science and Technology, 2020, 9, 015014.	0.9	4

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19	Prefaceâ€”JSS Focus Issue on Recent Advances in Wide Bandgap III-Nitride Devices and Solid State Lighting: A Tribute to Isamu Akasaki. ECS Journal of Solid State Science and Technology, 2020, 9, 010001.	0.9	0
20	The 2020 UV emitter roadmap. Journal Physics D: Applied Physics, 2020, 53, 503001.	1.3	289
21	Electrical properties of (11-22) Si:AlGaIn layers at high Al contents grown by metal-organic vapor phase epitaxy. Applied Physics Letters, 2020, 117, .	1.5	13
22	Electrical compensation and cation vacancies in Al rich Si-doped AlGaIn. Applied Physics Letters, 2020, 117, .	1.5	11
23	Milliwatt power 233â€”nm AlGaIn-based deep UV-LEDs on sapphire substrates. Applied Physics Letters, 2020, 117, .	1.5	50
24	Calculation of optical gain in AlGaIn quantum wells for ultraviolet emission. AIP Advances, 2020, 10, .	0.6	10
25	Advances in electron channelling contrast imaging and electron backscatter diffraction for imaging and analysis of structural defects in the scanning electron microscope. IOP Conference Series: Materials Science and Engineering, 2020, 891, 012023.	0.3	0
26	Reliability of UVC LEDs fabricated on AlN/sapphire templates with different threading dislocation densities. Applied Physics Letters, 2020, 117, .	1.5	34
27	Vertical conductivity and Pooleâ€”Frenkel-ionization of Mg acceptors in AlGaIn short-period superlattices with high Al mole fraction. Applied Physics Letters, 2020, 117, .	1.5	14
28	Low resistance n-contact for UVC LEDs by a two-step plasma etching process. Semiconductor Science and Technology, 2020, 35, 095019.	1.0	7
29	Enhanced wall plug efficiency of AlGaIn-based deep-UV LEDs using Mo/Al as p-contact. IEEE Photonics Technology Letters, 2020, , 1-1.	1.3	9
30	Thin-film flip-chip UVB LEDs realized by electrochemical etching. Applied Physics Letters, 2020, 116, 121101.	1.5	13
31	Status and Prospects of AlN Templates on Sapphire for Ultraviolet Lightâ€”Emitting Diodes. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1901022.	0.8	34
32	Polarization fields in semipolar ( 20 2 Å <sup>-1</sup> Å <sup>-1</sup> ) and ( 20 2 Å <sup>-1</sup> 1 ) InGaIn light emitting diodes. Applied Physics Letters, 2020, 116, 062106.	1.5	0
33	Structural and luminescence imaging and characterisation of semiconductors in the scanning electron microscope. Semiconductor Science and Technology, 2020, 35, 054001.	1.0	7
34	A Short Introduction to Semiconductor Nanophotonics. Springer Series in Solid-state Sciences, 2020, , 1-11.	0.3	2
35	Group III-Nitride-Based UV Laser Diodes. Springer Series in Solid-state Sciences, 2020, , 505-548.	0.3	2
36	Continuous-wave operation of DFB laser diodes based on GaIn using 10 <sup>5</sup> th-order laterally coupled surface gratings. Optics Letters, 2020, 45, 935.	1.7	10

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37	Improved performance of UVC-LEDs by combination of high-temperature annealing and epitaxially laterally overgrown AlN/sapphire. <i>Photonics Research</i> , 2020, 8, 589.	3.4	49
38	Electrical properties and microstructure formation of V/Al-based n-contacts on high Al mole fraction n-AlGaIn layers. <i>Photonics Research</i> , 2020, 8, 1381.	3.4	33
39	Reducing the grain density in semipolar (11-22) AlGaIn surfaces on m-plane sapphire substrates. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SC1026.	0.8	8
40	Effect of quantum barrier composition on electro-optical properties of AlGaIn-based UVC light emitting diodes. <i>Semiconductor Science and Technology</i> , 2019, 34, 085007.	1.0	6
41	Influence of substrate off-cut angle on the performance of 310-nm light emitting diodes. <i>Journal of Crystal Growth</i> , 2019, 526, 125241.	0.7	10
42	Determination of Sapphire Off-Cut and Its Influence on the Morphology and Local Defect Distribution in Epitaxially Laterally Overgrown AlN for Optically Pumped UVC Lasers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1900682.	0.8	13
43	Hole injection mechanism in the quantum wells of blue light emitting diode with V pits for micro-display application. <i>Applied Physics Express</i> , 2019, 12, 102016.	1.1	6
44	Electrochemical etching of AlGaIn for the realization of thin-film devices. <i>Applied Physics Letters</i> , 2019, 115, 182103.	1.5	20
45	High-Current Stress of UV-B (In)AlGaIn-Based LEDs: Defect-Generation and Diffusion Processes. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 3387-3392.	1.6	24
46	Optical light polarization and light extraction efficiency of AlGaIn-based LEDs emitting between 264 and 220nm. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SCCB20.	0.8	44
47	Influence of InN and AlN concentration on the compositional inhomogeneity and formation of InN-rich regions in In <sub>x</sub> Al <sub>y</sub> Ga <sub>1-x-y</sub> N. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SCCB18.	0.8	3
48	Indium incorporation in quaternary In <sub>x</sub> Al <sub>y</sub> Ga <sub>1-x-y</sub> N for UVB-LEDs. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SC1004.	0.8	5
49	Precise determination of polarization fields in c-plane GaN/Al <sub>x</sub> Ga <sub>1-x</sub> N/GaN heterostructures with capacitance-voltage-measurements. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SCCB08.	0.8	3
50	Degradation of (In)AlGaIn-Based UVB LEDs and Migration of Hydrogen. <i>IEEE Photonics Technology Letters</i> , 2019, 31, 529-532.	1.3	43
51	The emergence and prospects of deep-ultraviolet light-emitting diode technologies. <i>Nature Photonics</i> , 2019, 13, 233-244.	15.6	800
52	Displacement Talbot lithography for nano-engineering of III-nitride materials. <i>Microsystems and Nanoengineering</i> , 2019, 5, 52.	3.4	33
53	Influence of light absorption on the performance characteristics of UV LEDs with emission between 239 and 217 nm. <i>Applied Physics Express</i> , 2019, 12, 012008.	1.1	34
54	Inhomogeneous spectral broadening in deep ultraviolet light emitting diodes. , 2019, , .		5

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55	MOVPE-grown AlGaIn-based tunnel heterojunctions enabling fully transparent UVC LEDs. Photonics Research, 2019, 7, B7.	3.4	42
56	Current-induced degradation and lifetime prediction of 310-nm ultraviolet light-emitting diodes. Photonics Research, 2019, 7, B36.	3.4	46
57	Scanning electron microscopy as a flexible technique for investigating the properties of UV-emitting nitride semiconductor thin films. Photonics Research, 2019, 7, B73.	3.4	9
58	On the optical polarization properties of semipolar (202°) and (202°) InGaIn/GaN quantum wells. Journal of Applied Physics, 2018, 123, .	1.1	7
59	DFB Laser Diodes Based on GaN Using 10th Order Laterally Coupled Surface Gratings. IEEE Photonics Technology Letters, 2018, 30, 231-234.	1.3	31
60	AlGaIn-based deep UV LEDs grown on sputtered and high temperature annealed AlN/sapphire. Applied Physics Letters, 2018, 112, .	1.5	171
61	Influence of template properties and quantum well number on stimulated emission from Al <sub>0.7</sub> Ga <sub>0.3</sub> N/Al <sub>0.8</sub> Ga <sub>0.2</sub> N quantum wells. Semiconductor Science and Technology, 2018, 33, 035015.	1.0	3
62	MOVPE Growth of Smooth and Homogeneous Al <sub>0.8</sub> Ga <sub>0.2</sub> N:Si Superlattices as UVC Laser Cladding Layers. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1800005.	0.8	7
63	Degradation effects of the active region in UV-C light-emitting diodes. Journal of Applied Physics, 2018, 123, .	1.1	55
64	Effect of the GaIn:Mg Contact Layer on the Light Output and Current-Voltage Characteristic of UVB LEDs. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700643.	0.8	18
65	AlGaIn multi-quantum barriers for electron blocking in group III-nitride devices. , 2018, , .		0
66	Bow Reduction of AlInGaIn-Based Deep UV LED Wafers Using Focused Laser Patterning. IEEE Photonics Technology Letters, 2018, 30, 1792-1794.	1.3	2
67	Accurate determination of polarization fields in (0001) c-plane InAlIn/GaN heterostructures with capacitance-voltage-measurements. Journal Physics D: Applied Physics, 2018, 51, 485103.	1.3	5
68	Localization of current-induced degradation effects in (InAlGa)N-based UV-B LEDs. Journal of Applied Physics, 2018, 124, .	1.1	22
69	Auger recombination in AlGaIn quantum wells for UV light-emitting diodes. Applied Physics Letters, 2018, 113, .	1.5	59
70	Influence of waveguide strain and surface morphology on AlGaIn-based deep UV laser characteristics. Journal Physics D: Applied Physics, 2018, 51, 415101.	1.3	16
71	Degradation behavior of AlGaIn-based 233 nm deep-ultraviolet light emitting diodes. Semiconductor Science and Technology, 2018, 33, 095017.	1.0	18
72	10th order laterally coupled GaIn-based DFB laser diodes with V-shaped surface gratings. , 2018, , .		3

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73	Defect-generation and diffusion in (In)AlGa <sub>N</sub> -based UV-B LEDs submitted to constant current stress. , 2018, , .		3
74	From heterostructure design to package: development of efficient and reliable UVB LEDs (Conference) Tj ETQq0 0 0 rgBT /Overlock 10 T		
75	Metamorphic Al <sub>0.5</sub> Ga <sub>0.5</sub> N:Si on AlN/sapphire for the growth of UVB LEDs. Journal of Crystal Growth, 2017, 464, 185-189.	0.7	38
76	Analysis of doping concentration and composition in wide bandgap AlGa <sub>N</sub> :Si by wavelength dispersive x-ray spectroscopy. Semiconductor Science and Technology, 2017, 32, 035020.	1.0	13
77	The effects of magnesium doping on the modal loss in AlGa <sub>N</sub> -based deep UV lasers. Applied Physics Letters, 2017, 110, .	1.5	33
78	Improved light extraction and quantum efficiencies for UVB LEDs with UV-transparent p-AlGa <sub>N</sub> superlattices (Conference Presentation). , 2017, , .		5
79	Surface reconstructions of (0001) AlN during metal-organic vapor phase epitaxy. Physica Status Solidi (B): Basic Research, 2017, 254, 1600711.	0.7	7
80	Growth and Optical Properties of GaN-Based Non- and Semipolar LEDs. Topics in Applied Physics, 2017, , 93-128.	0.4	1
81	Defect generation in deep-UV AlGa <sub>N</sub> -based LEDs investigated by electrical and spectroscopic characterisation. Proceedings of SPIE, 2017, , .	0.8	3
82	Design considerations for AlGa <sub>N</sub> -based UV LEDs emitting near 235 nm with uniform emission pattern. Semiconductor Science and Technology, 2017, 32, 045019.	1.0	4
83	Optically Pumped DFB Lasers Based on GaN Using 10th-Order Laterally Coupled Surface Gratings. IEEE Photonics Technology Letters, 2017, 29, 138-141.	1.3	16
84	Defect-Related Degradation of AlGa <sub>N</sub> -Based UV-B LEDs. IEEE Transactions on Electron Devices, 2017, 64, 200-205.	1.6	62
85	Effect of Cl <sub>2</sub> plasma treatment and annealing on vanadium based metal contacts to Si-doped Al <sub>0.75</sub> Ga <sub>0.25</sub> N. Journal of Applied Physics, 2017, 122, .	1.1	11
86	Controlling the morphology transition between step-flow growth and step-bunching growth. Journal of Crystal Growth, 2017, 478, 187-192.	0.7	47
87	Chip design for thin-film deep ultraviolet LEDs fabricated by laser lift-off of the sapphire substrate. Semiconductor Science and Technology, 2017, 32, 12LT01.	1.0	14
88	Gas Sensing of Nitrogen Oxide Utilizing Spectrally Pure Deep UV LEDs. IEEE Journal of Selected Topics in Quantum Electronics, 2017, 23, 29-36.	1.9	43
89	Highly Reflective p-Contacts Made of Pd-Al on Deep Ultraviolet Light-Emitting Diodes. IEEE Photonics Technology Letters, 2017, 29, 2222-2225.	1.3	14
90	Recombination mechanisms and thermal droop in AlGa <sub>N</sub> -based UV-B LEDs. Photonics Research, 2017, 5, A44.	3.4	36

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91	A Miniaturized UV-LED Based Optical Gas Sensor Utilizing Silica Waveguides for the Measurement of Nitrogen Dioxide and Sulphur Dioxide. Proceedings (mdpi), 2017, 1, .	0.2	2
92	Effect of Electron Blocking Layer Doping and Composition on the Performance of 310 nm Light Emitting Diodes. Materials, 2017, 10, 1396.	1.3	17
93	Correlation of sapphire off- $\theta$ cut and reduction of defect density in MOVPE grown AlN. Physica Status Solidi (B): Basic Research, 2016, 253, 809-813.	0.7	35
94	Low absorption loss p-AlGaIn superlattice cladding layer for current-injection deep ultraviolet laser diodes. Applied Physics Letters, 2016, 108, .	1.5	47
95	On the formation of cleaved mirror facets of GaN-based laser diodes—A comparative study of diamond-tip edge-scribing and laser scribing. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2016, 34, .	0.6	6
96	Electronic properties of Si-doped Al <sub>x</sub> Ga <sub>1-x</sub> N with aluminum mole fractions above 80%. Journal of Applied Physics, 2016, 120, .	1.1	47
97	Dominance of radiative recombination from electron-beam-pumped deep-UV AlGaIn multi-quantum-well heterostructures. Applied Physics Letters, 2016, 109, .	1.5	32
98	Determination of polarization fields in group III-nitride heterostructures by capacitance-voltage-measurements. Journal of Applied Physics, 2016, 119, .	1.1	9
99	Role of substrate quality on the performance of semipolar (112̂2) InGaIn light-emitting diodes. Journal of Applied Physics, 2016, 120, .	1.1	8
100	Comparison of fabrication methods for microstructured deep UV multimode waveguides based on fused silica. Proceedings of SPIE, 2016, , .	0.8	0
101	Surface properties of AlInGaIn/GaN heterostructure. Materials Science in Semiconductor Processing, 2016, 55, 26-31.	1.9	9
102	MOVPE growth and indium incorporation of polar, semipolar (112) and (201)̂%InGaIn. Physica Status Solidi (B): Basic Research, 2016, 253, 93-98.	0.7	5
103	Embedded GaIn nanostripes on c/sapphire for DFB lasers with semipolar quantum wells. Physica Status Solidi (B): Basic Research, 2016, 253, 180-185.	0.7	5
104	Efficient carrier injection and electron confinement in UV-B light-emitting diodes. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 210-214.	0.8	21
105	Impact of inhomogeneous broadening on optical polarization of high-inclination semipolar and nonpolar $\ln_x\text{Al}_{1-x}\text{N}$ quantum wells. Physical Review B, 2016, 93, .		
106	Impact of acceptor concentration on the resistivity of Ni/Au p-contacts on semipolar (20̂21) GaIn:Mg. Physica Status Solidi (B): Basic Research, 2016, 253, 169-173.	0.7	9
107	On optical polarization and charge carrier statistics of nonpolar InGaIn quantum wells. Physica Status Solidi (B): Basic Research, 2016, 253, 145-157.	0.7	7
108	Influence of the LED heterostructure on the degradation behavior of (InAlGa)N-based UV-B LEDs. Proceedings of SPIE, 2016, , .	0.8	1

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109	Preparation and structure of ultra-thin GaN (0001) layers on In <sub>0.11</sub> Ga <sub>0.89</sub> N-single quantum wells. <i>Materials Science in Semiconductor Processing</i> , 2016, 55, 7-11.	1.9	12
110	A Brief Review of III-Nitride UV Emitter Technologies and Their Applications. <i>Springer Series in Materials Science</i> , 2016, , 1-25.	0.4	60
111	V-pit to truncated pyramid transition in AlGaIn-based heterostructures. <i>Semiconductor Science and Technology</i> , 2015, 30, 114010.	1.0	19
112	Temperature induced degradation of InAlGaIn multiple-quantum well UV-B LEDs. <i>Materials Research Society Symposia Proceedings</i> , 2015, 1792, 1.	0.1	6
113	Spatial clustering of defect luminescence centers in Si-doped low resistivity Al <sub>0.82</sub> Ga <sub>0.18</sub> N. <i>Applied Physics Letters</i> , 2015, 107, .	1.5	22
114	Degradation of (InAlGa)N-based UV-B light emitting diodes stressed by current and temperature. <i>Journal of Applied Physics</i> , 2015, 118, .	1.1	47
115	Strongly transverse-electric-polarized emission from deep ultraviolet AlGaIn quantum well light emitting diodes. <i>Applied Physics Letters</i> , 2015, 107, .	1.5	79
116	Spatial inhomogeneities in Al <sub>x</sub> Ga <sub>1-x</sub> N quantum wells induced by the surface morphology of AlN/sapphire templates. <i>Semiconductor Science and Technology</i> , 2015, 30, 114008.	1.0	13
117	In-situ observation of InGaIn quantum well decomposition during growth of laser diodes. <i>Crystal Research and Technology</i> , 2015, 50, 499-503.	0.6	11
118	Desorption induced GaIn quantum dots on (0001) AlN by MOVPE. <i>Physica Status Solidi - Rapid Research Letters</i> , 2015, 9, 526-529.	1.2	9
119	Quality CuInSe <sub>2</sub> and Cu(In,Ga)Se <sub>2</sub> thin films processed by single-step electrochemical deposition techniques. <i>Materials Research Express</i> , 2015, 2, 056402.	0.8	6
120	Optically pumped low-threshold UV lasers. , 2015, , .		0
121	III-nitride deep UV laser on sapphire substrate. , 2015, , .		0
122	Index-Antiguinding in Narrow-Ridge GaIn-Based Laser Diodes Investigated by Measurements of the Current-Dependent Gain and Index Spectra and by Self-Consistent Simulation. <i>IEEE Journal of Quantum Electronics</i> , 2015, 51, 1-6.	1.0	5
123	Current spreading in UV-C LEDs emitting at 235 nm. <i>Proceedings of SPIE</i> , 2015, , .	0.8	1
124	Effect of heterostructure design on carrier injection and emission characteristics of 295-nm light emitting diodes. <i>Journal of Applied Physics</i> , 2015, 117, .	1.1	32
125	Anisotropic optical properties of semipolar AlGaIn layers grown on m-plane sapphire. <i>Applied Physics Letters</i> , 2015, 106, .	1.5	17
126	High-power UV-B LEDs with long lifetime. <i>Proceedings of SPIE</i> , 2015, , .	0.8	41





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145	Controlled coalescence of MOVPE grown AlN during lateral overgrowth. Journal of Crystal Growth, 2013, 368, 83-86.	0.7	38
146	Determination of lattice parameters, strain state and composition in semipolar III-nitrides using high resolution X-ray diffraction. Journal of Applied Physics, 2013, 114, .	1.1	35
147	Excitonic recombination in epitaxial lateral overgrown AlN on sapphire. Applied Physics Letters, 2013, 103, .	1.5	17
148	Ohmic Contacts on N-Face n-Type GaN After Low Temperature Annealing. IEEE Photonics Technology Letters, 2013, 25, 1278-1281.	1.3	10
149	Role of nitridation on polarity and growth of InN by metal-organic vapor phase epitaxy. Journal of Crystal Growth, 2013, 376, 17-22.	0.7	5
150	Energetics of Quantum Dot Formation and Relaxation of InGaAs on GaAs(001). Japanese Journal of Applied Physics, 2013, 52, 041201.	0.8	7
151	Effective Thermal Management in Ultraviolet Light-Emitting Diodes With Micro-LED Arrays. IEEE Transactions on Electron Devices, 2013, 60, 782-786.	1.6	68
152	Structural and optical properties of semipolar AlGaIn grown on sapphire by metal-organic vapor phase epitaxy. Journal of Crystal Growth, 2013, 367, 42-47.	0.7	40
153	Growth mode transition and relaxation of thin InGaIn layers on GaN (0001). Journal of Crystal Growth, 2013, 372, 65-72.	0.7	19
154	High quality AlGaIn grown on ELO AlN/sapphire templates. Journal of Crystal Growth, 2013, 377, 32-36.	0.7	89
155	Improved injection efficiency in 290-nm light emitting diodes with Al(Ga)N electron blocking heterostructure. Applied Physics Letters, 2013, 103, .	1.5	44
156	Growth and characterization of stacking fault reduced GaN (1,0,ar{1},3) on sapphire. Journal Physics D: Applied Physics, 2013, 46, 125308.	1.3	12
157	Electrical properties and microstructure of vanadium-based contacts on ICP plasma etched n-type AlGaIn:Si and GaIn:Si surfaces. Semiconductor Science and Technology, 2013, 28, 125015.	1.0	37
158	Index antiguiding in narrow ridge-waveguide (In,Al)GaIn-based laser diodes. Journal of Applied Physics, 2013, 114, .	1.1	8
159	Highly conductive n-Al <sub>x</sub> In <sub>1-x</sub> N layers with aluminum mole fractions above 80%. Applied Physics Letters, 2013, 103, .	1.5	86
160	Polarity determination of polar and semipolar (112̂2)â€‰InN and GaN layers by valence band photoemission spectroscopy. Journal of Applied Physics, 2013, 114, .	1.1	30
161	Surface Transitions During InGaIn Growth on GaN(0001) in Metal-Organic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2013, 52, 08JB23.	0.8	6
162	Nucleation and Coalescence of Indium Rich InGaIn Layers on Nitridated Sapphire in Metal-Organic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2013, 52, 08JD03.	0.8	4



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181	Surface diffusion and layer morphology of ((112 $\hat{A}$ <sup>2</sup> )) GaN grown by metal-organic vapor phase epitaxy. Journal of Applied Physics, 2012, 111, .	1.1	48
182	Comparison study of N $\hat{A}$ and In $\hat{A}$ polar {0001} InN layers grown by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 977-981.	0.8	6
183	Optically pumped UV lasers grown on bulk AlN substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 822-825.	0.8	69
184	Spectral properties of polarized light from semipolar grown InGaN quantum wells at low temperatures. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 700-703.	0.8	2
185	Investigation of inversion domain formation in AlN grown on sapphire by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 496-498.	0.8	20
186	Mobility-limiting mechanisms in polar semiconductor heterostructures. Acta Materialia, 2012, 60, 3176-3180.	3.8	8
187	Towards sub-300 nm laser diodes on bulk AlN substrates. , 2011, , .		0
188	Strong charge carrier localization interacting with extensive nonradiative recombination in heteroepitaxially grown m-plane GaInN quantum wells. Semiconductor Science and Technology, 2011, 26, 105017.	1.0	10
189	Advances in group III-nitride-based deep UV light-emitting diode technology. Semiconductor Science and Technology, 2011, 26, 014036.	1.0	593
190	9.1 Laser diodes in the visible spectral range: GaN-based blue and green laser diodes. Landolt-B $\hat{A}$ <sup>3</sup> $\hat{A}$ <sup>6</sup> , rnsstein - Group VIII Advanced Materials and Technologies, 2011, , 22-37.	0.0	0
191	Adsorbate-induced modification of the surface electronic structure at GaAs(001) surfaces. Physical Review B, 2011, 83, .	1.1	8
192	High gain ultraviolet photodetectors based on AlGaIn/GaN heterostructures for optical switching. Applied Physics Letters, 2011, 98, .	1.5	90
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